

Commercial Space Product GaAs, pHEMT, MMIC, Low Noise Amplifier, 23 GHz to 31 GHz

## FEATURES

- ▶ Low noise figure: 1.6 dB typical at 27 GHz to 31 GHz
- ▶ Single positive supply (self biased)
- ▶ High gain: 27 dB typical at 27 GHz to 31 GHz
- ▶ High OIP3: 21.5 dBm typical at 27 GHz to 31 GHz
- ▶ RoHS-compliant, 2 mm × 2 mm, 8-lead LFCSP

## COMMERCIAL SPACE FEATURES

- ▶ Wafer diffusion lot traceability
- ▶ Radiation lot acceptance test (RLAT)
  - ▶ Total ionizing dose (TID)
- ▶ Radiation benchmark
  - ▶ Single event latch-up (SEL)

## APPLICATIONS

- ▶ Geosynchronous high throughput satellite (GEO HTS)
- ▶ Low Earth orbit (LEO) space payloads
- ▶ Satellite communication

## GENERAL DESCRIPTION

The ADL8142S-CSL is a gallium arsenide (GaAs), monolithic microwave integrated circuit (MMIC), pseudomorphic high electron mobility transistor (pHEMT), low noise wideband amplifier that operates from 23 GHz to 31 GHz. The ADL8142S-CSL provides a typical gain of 27 dB, a 1.6 dB typical noise figure, and a typical output third-order intercept (OIP3) of 21.5 dBm at 27 GHz to 31 GHz, requiring only 25 mA from a 2 V supply voltage. Note that the OIP3 can be improved with larger drain currents. The ADL8142S-CSL also features inputs and outputs that are ac-coupled and internally matched to 50 Ω, making it ideal for high capacity microwave radio applications.

The ADL8142S-CSL is housed in a [RoHS-compliant, 2 mm × 2 mm, 8-lead LFCSP](#). Additional application and technical information can be found in the [Commercial Space Products Program](#) brochure and the [ADL8142](#) data sheet.

## FUNCTIONAL BLOCK DIAGRAM

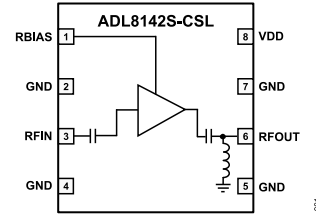


Figure 1. Functional Block Diagram

Rev. 0

DOCUMENT FEEDBACK

TECHNICAL SUPPORT

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**REVISION HISTORY****6/2022—Revision 0: Initial Version**

## SPECIFICATIONS

## 23 GHZ TO 27 GHZ FREQUENCY RANGE

Supply voltage ( $V_{DD}$ ) = 2 V, quiescent current ( $I_{DQ}$ ) = 25 mA, bias resistance ( $R_{BIAS}$ ) = 634  $\Omega$ , and  $T_C$  = 25°C, unless otherwise noted.

Table 1.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
FREQUENCY RANGE	23		27	GHz	
GAIN		29		dB	
Gain Variation over Temperature		0.073		dB/°C	
NOISE FIGURE		1.8		dB	
RETURN LOSS					
Input (S11)		10.5		dB	
Output (S22)		16		dB	
OUTPUT					
Power for 1 dB Compression (P1dB)		8.5		dBm	
Saturated Power ( $P_{SAT}$ )		10		dBm	
IP3		17.5		dBm	Measurement taken at output power ( $P_{OUT}$ ) per tone = -4 dBm
Second-Order Intercept (IP2)		25		dBm	Measurement taken at $P_{OUT}$ per tone = -4 dBm
POWER ADDED EFFICIENCY (PAE)		18		%	Measured at $P_{SAT}$

## 27 GHZ TO 31 GHZ FREQUENCY RANGE

$V_{DD}$  = 2 V,  $I_{DQ}$  = 25 mA,  $R_{BIAS}$  = 634  $\Omega$ , and  $T_C$  = 25°C, unless otherwise noted.

Table 2.

Parameter	Min	Typ	Max	Unit	Test Conditions/Comments
FREQUENCY RANGE	27		31	GHz	
GAIN	24.5	27		dB	
Gain Variation over Temperature		0.037		dB/°C	
NOISE FIGURE		1.6		dB	
RETURN LOSS					
S11		13		dB	
S22		15		dB	
OUTPUT					
P1dB	7.5	10		dBm	
$P_{SAT}$		11		dBm	
IP3		21.5		dBm	Measurement taken at $P_{OUT}$ per tone = -4 dBm
IP2		35		dBm	Measurement taken at $P_{OUT}$ per tone = -4 dBm
PAE		21		%	Measured at $P_{SAT}$

## DC SPECIFICATIONS

Table 3.

Parameter	Min	Typ	Max	Unit
SUPPLY CURRENT				
$I_{DQ}$		25		mA
Amplifier Current ( $I_{DQ\_AMP}$ )		23		mA
RBIAS Current ( $I_{RBIAS}$ )		2		mA
SUPPLY VOLTAGE				
$V_{DD}$	1.5	2	3.5	V

## SPECIFICATIONS

## RADIATION TEST AND LIMIT SPECIFICATIONS

Electrical characteristics at  $V_{DD} = 2\text{ V}$ ,  $I_{DQ} = 25\text{ mA}$ ,  $R_{BIAS} = 634\ \Omega$ , and  $T_C = 25^\circ\text{C}$ , unless otherwise noted. Total ionizing dose (TID) testing characterized to 30 krad.

Table 4.

Parameter	Min	Typ	Max	Unit
FREQUENCY RANGE	27		31	GHz
GAIN	24.5	27		GHz
OUTPUT P1dB	7	10		dBm
SUPPLY CURRENT $I_{DQ}$		25		mA
SUPPLY VOLTAGE $V_{DD}$	1.5	2	3.5	V

## ABSOLUTE MAXIMUM RATINGS

Table 5.

Parameter	Rating
$V_{DD}$	4.5 V
RF Input Power (RFIN)	20 dBm
Pulsed RFIN (Duty Cycle = 10%, Pulse Width = 100 $\mu$ s)	22 dBm
Continuous Power Dissipation ( $P_{DISS}$ ), $T_{CASE} = 85^{\circ}\text{C}$ (Derate 5.99 mW/ $^{\circ}\text{C}$ Above 85 $^{\circ}\text{C}$ )	0.54 W
Temperature	
Storage Range	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$
Operating Range	-40 $^{\circ}\text{C}$ to +85 $^{\circ}\text{C}$
Nominal Junction ( $T_A = 85^{\circ}\text{C}$ , $V_{DD} = 2\text{ V}$ , $I_{DQ} = 25\text{ mA}$ , Input Power ( $P_{IN}$ ) = Off)	93.4 $^{\circ}\text{C}$
Maximum Junction	175 $^{\circ}\text{C}$

Stresses at or above those listed under Absolute Maximum Ratings may cause permanent damage to the product. This is a stress rating only; functional operation of the product at these or any other conditions above those indicated in the operational section of this specification is not implied. Operation beyond the maximum operating conditions for extended periods may affect product reliability.

## THERMAL RESISTANCE

Thermal performance is directly linked to printed circuit board (PCB) design and operating environment. Close attention to PCB thermal design is required.

$\theta_{JC}$  is the junction to case thermal resistance.

Table 6. Thermal Resistance

Package Type	$\theta_{JC}$	Unit
CP-8-30		
Quiescent, $T_{BASE} = 25^{\circ}\text{C}$	134.3	$^{\circ}\text{C}/\text{W}$
Worst Case <sup>1</sup> , $T_{BASE} = 85^{\circ}\text{C}$	167	$^{\circ}\text{C}/\text{W}$

<sup>1</sup> Worst case across all specified operating conditions

## OUTGAS TESTING

The criteria used for the acceptance and rejection of materials must be determined by the user and based upon specific component and system requirements. Historically, a total mass loss (TML) of 1.00% and collected volatile condensable material (CVCM) of 0.10% have been used as screening levels for rejection of spacecraft materials.

Table 7. Outgas Testing

Specification (Tested per ASTM E595 -15)	Value	Unit
Total Mass Lost	0.14	%
Collected Volatile Condensable Material	0.01	%
Water Vapor Recovered	0.03	%

## ELECTROSTATIC DISCHARGE (ESD) RATINGS

The following ESD information is provided for handling of ESD-sensitive devices in an ESD protected area only.

Human body model (HBM) per ANSI/ESDA/JEDEC JS-001.

## ESD Ratings for ADL8142S-CSL

Table 8. ADL8142S-CSL, 8-Lead LFCSP

ESD Model	Withstand Threshold (V)	Class
HBM	$\pm 250$	1A

## ESD CAUTION



**ESD (electrostatic discharge) sensitive device.** Charged devices and circuit boards can discharge without detection. Although this product features patented or proprietary protection circuitry, damage may occur on devices subjected to high energy ESD. Therefore, proper ESD precautions should be taken to avoid performance degradation or loss of functionality.

## PIN CONFIGURATION AND FUNCTION DESCRIPTIONS

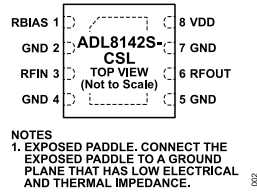


Figure 2. Pin Configuration

Table 9. Pin Function Descriptions

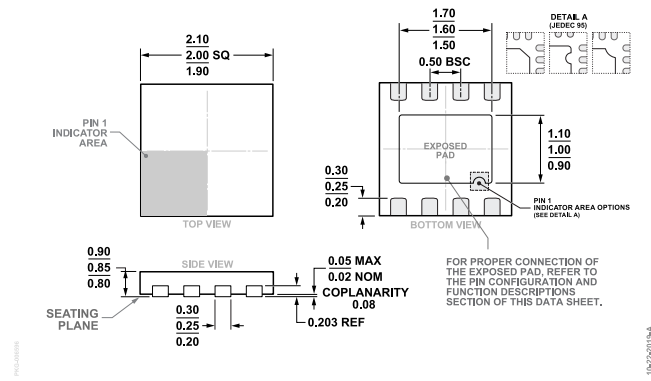
Pin No.	Mnemonic	Description
1	RBIAS	Bias Setting Resistor. Connect a resistor between RBIAS and VDD to set the $I_{DQ}$ . See the typical application circuit and the recommended bias resistor values for $V_{DD} = 2\text{ V}$ table in the <a href="#">ADL8142</a> data sheet for more details.
2, 4, 5, 7	GND	Ground. Connect the GND pins to a ground plane that has low electrical and thermal impedance.
3	RFIN	RF Input. The RFIN pin is ac-coupled and matched to $50\ \Omega$ .
6	RFOUT	RF Output. The RFOUT pin is ac-coupled and matched to $50\ \Omega$ .
8	VDD	Drain Bias. Connect the VDD pin to the supply voltage.
	EXPOSED PADDLE	Exposed Paddle. Connect the exposed paddle to a ground plane that has low electrical and thermal impedance.

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**TYPICAL PERFORMANCE CHARACTERISTICS**

See the [ADL8142](#) data sheet for the typical performance characteristics plots.

OUTLINE DIMENSIONS



**Figure 3. 8-Lead Lead Frame Chip Scale Package [LFCSP]  
2 mm × 2 mm Body and 0.85 mm Package Height  
(CP-8-30)  
Dimensions shown in millimeters**

ORDERING GUIDE

Model <sup>1</sup>	Temperature Range	Package Description	Packing Quantity	Package Option
ADL8142ACPZN-CSL	-40°C to +85°C	8-Lead LFCSP, 2 mm × 2 mm × 0.85	Reel, 500	CP-8-30
ADL8142ACPZN-R7-CSL	-40°C to +85°C	8-Lead LFCSP, 2 mm × 2 mm × 0.85	Reel, 500	CP-8-30

<sup>1</sup> Z = RoHS Compliant Part.